

N-Channel JFET, -25 V, 20 to 40 mA, 40 mS NSVJ3910SB3

Automotive JFET designed for compact and efficient designs and including high gain performance. AEC-Q101 qualified JFET and PPAP capable suitable for automotive applications.

Features

- High Forward Transfer Admittance
- High Breakdown Voltage
- Low Input Capacitance
- Low Noise Figure
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

Typical Applications

• Low Noise Amplifier for Automotive AM Radio

Specifications

ABSOLUTE MAXIMUM RATINGS (at $T_A = 25$ °C)

Parameter	Symbol	Value	Unit	
Drain-to-Source Voltage	V_{DSX}	25	V	
Gate-to-Drain Voltage	V_{GDS}	-25	V	
Gate Current	I _G	10	mA	
Drain Current	I _D	50	mA	
Allowable Power Dissipation	P_{D}	400	mW	
Operating Junction and Storage Temperature	T _J , T _{STG}	-55 to +150	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

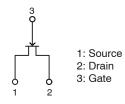


MARKING DIAGRAM



J2 = Specific Device Code

ELECTRICAL CONNECTION



N-Channel

ORDERING INFORMATION

Device	Package	Shipping [†]
NSVJ3910SB3T1G	CPH3 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (at $T_A = 25^{\circ}C$)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Gate-to-Drain Breakdown Voltage	V _{(BR)GDS}	$I_G = -10 \ \mu A, \ V_{DS} = 0 \ V$	-25	-	-	V
Gate Cutoff Current	I _{GSS}	V _{GS} = -10 V, V _{DS} = 0 V	-	-	-1.0	nA
Cutoff Voltage	V _{GS(off)}	$V_{DS} = 5 \text{ V}, I_D = 100 \mu\text{A}$	-0.6	-1.2	-1.8	V
Drain Current	I _{DSS}	V _{DS} = 5 V, V _{GS} = 0 V	20	-	40	mA
Forward Transfer Admittance	yfs	V _{DS} = 5 V, V _{GS} = 0 V, f = 1 kHz	30	40	-	mS
Input Capacitance	Ciss	V _{DS} = 5 V, V _{GS} = 0 V, f = 1 MHz	-	6.0	-	pF
Reverse Transfer Capacitance	Crss		-	2.3	-	pF
Noise Figure	NF	V _{DS} = 5 V, V _{GS} = 0 V, f = 100 MHz	-	2.1	2.8	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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TYPICAL CHARACTERISTICS

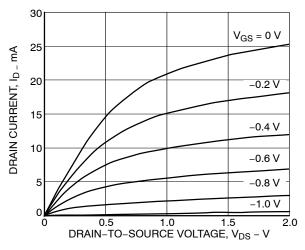


Figure 1. I_D - V_{DS}

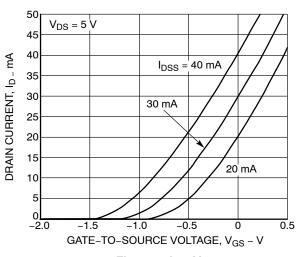
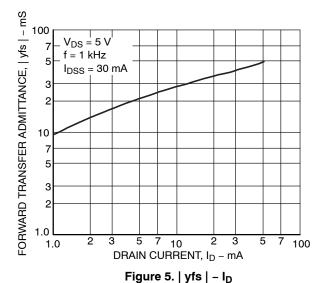


Figure 3. I_D - V_{GS}



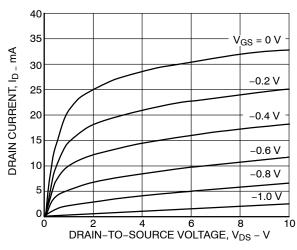


Figure 2. $I_D - V_{DS}$

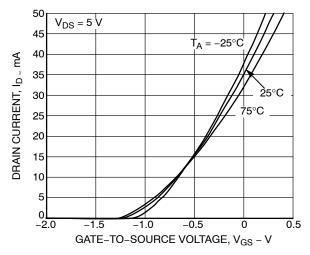


Figure 4. I_D - V_{GS}

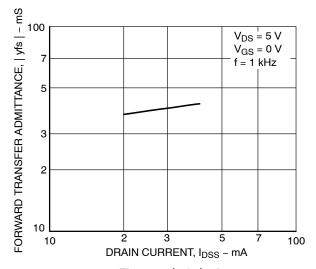
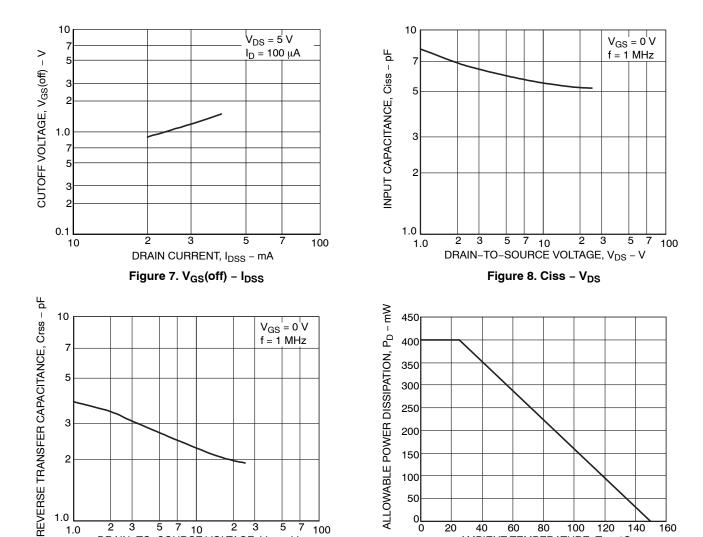


Figure 6. | yfs | - I_{DSS}

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TYPICAL CHARACTERISTICS (CONTINUED)

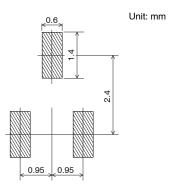


 $\frac{2}{2}$ $\frac{3}{5}$ $\frac{5}{7}$ $\frac{7}{10}$ $\frac{2}{10}$ $\frac{3}{10}$ $\frac{5}{10}$ DRAIN-TO-SOURCE VOLTAGE, V_{DS} - V

Figure 9. Crss - V_{DS}

1.0

RECOMMENDED SOLDERING FOOTPRINT



40 60 80 100 120 1 AMBIENT TEMPERATURE, T_A – °C

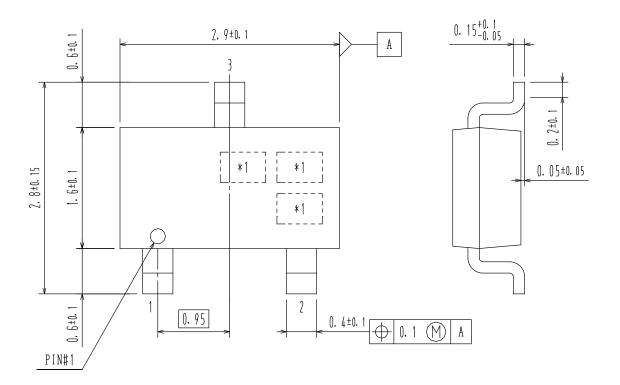
Figure 10. P_D - T_A

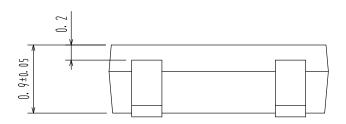
20

Figure 11. Recommended Soldering Footprint

CPH3 CASE 318BA ISSUE O

DATE 30 NOV 2011





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